



ACE17427B

N-Channel Enhancement Mode Power MOSFET

Features

- $V_{DS}= 40V$, $I_D=90A$
- $R_{DS(ON)}@ V_{GS} = 10V$, TYP=4.2m Ω
- $R_{DS(ON)}@ V_{GS} = 4.5V$, TYP=5.4m Ω

General Description

- load switching
- use in PWM
- general purpose applications

Absolute Maximum Ratings @ $T_A=25^\circ C$ unless otherwise noted

Parameter		Symbol	Max	Unit
Drain-Source Voltage		V_{DSS}	40	V
Gate-Source Voltage		V_{GSS}	± 20	V
Drain Current (Continuous)*AC	$T_C=25^\circ C$	I_D	90	A
	$T_C=70^\circ C$		62	
Drain Current (Pulsed)*B		I_{DM}	360	A
Avalanche energy L= 1 mH		EAS	162	mJ
Power Dissipation	$T_A=25^\circ C$	P_D	71	W
Operating temperature / Storage temperature		T_J/T_{STG}	-55~150	$^\circ C$

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in² FR-4 board with 2oz. Copper, in a still air environment with $T_A=25^\circ C$. The value in any given application depends on the user's specific board design.

B: Repetitive rating, pulse width limited by junction temperature.

C: The current rating is based on the $t \leq 10s$ junction to ambient thermal resistance rating.

Thermal Resistance Ratings

Parameter		Symbol	Maximum	Unit
Maximum Junction-to-Ambient	Steady State	R_{thJA}	62.5	$^\circ C/W$
Maximum Junction-to-Case (Drain)	Steady State	R_{thJC}	2.1	

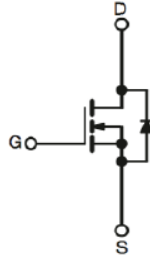
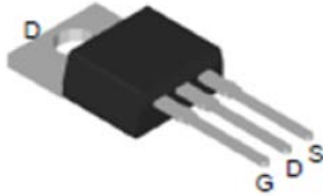


ACE17427B

N-Channel Enhancement Mode Power MOSFET

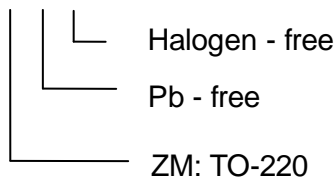
Packaging Type

TO-220



Ordering information

ACE17427B XX + H



Electrical Characteristics $T_A=25^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Static						
Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0V, I_D=250\mu A$	40			V
Zero gate voltage drain current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$			1	μA
Gate threshold voltage	$V_{GS(th)}$	$V_{GS}=V_{DS}, I_{DS}=250\mu A$	0.9	1.37	3	V
Gate leakage current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	μA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=20A$		4.2	5.5	m Ω
		$V_{GS}=4.5V, I_D=15A$		5.4	7.5	
Diode forward voltage	V_{SD}	$I_{SD}=20A, V_{GS}=0V$			1.5	V
Diode Forward Current	I_S	TC =25 $^\circ\text{C}$			90	A
Switching						
Total Gate Charge	Q_g	$V_{GS}=10V, V_{DS}=15V,$ $I_D=20A$		67		nC
Gate-Source Charge	Q_{gs}			10		
Gate-Drain Charge	Q_{gd}			12		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, I_D=2A,$ $V_{GS}=10V, R_G=3\Omega$		19		ns
Turn-on Rise Time	t_r			10		
Turn-off Delay Time	$t_{d(off)}$			84		
Turn-off Fall Time	t_f			22		
Dynamic						
Input Capacitance	C_{iss}	$V_{GS}=0V, V_{DS}=15V,$ $f=1.0\text{MHz}$		3070		pF
Output Capacitance	C_{oss}			385		
Reverse Transfer Capacitance	C_{rss}			285		



ACE17427B

N-Channel Enhancement Mode Power MOSFET

Typical Performance Characteristics

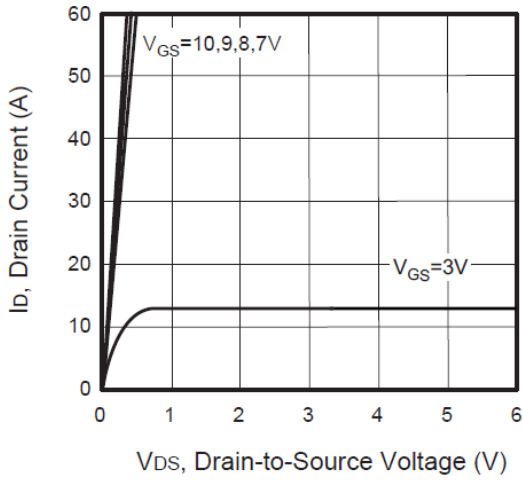


Figure 1. Output Characteristics

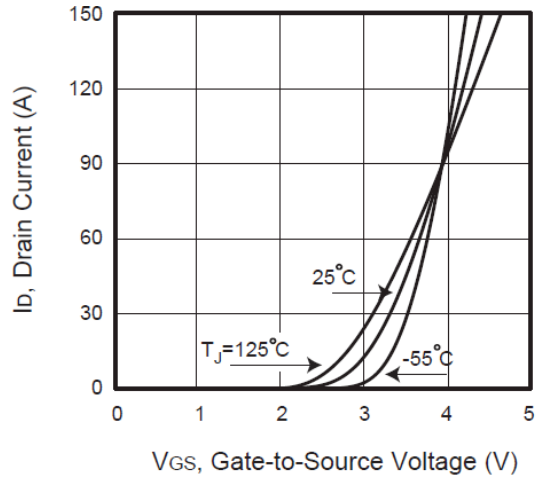


Figure 2. Transfer Characteristics

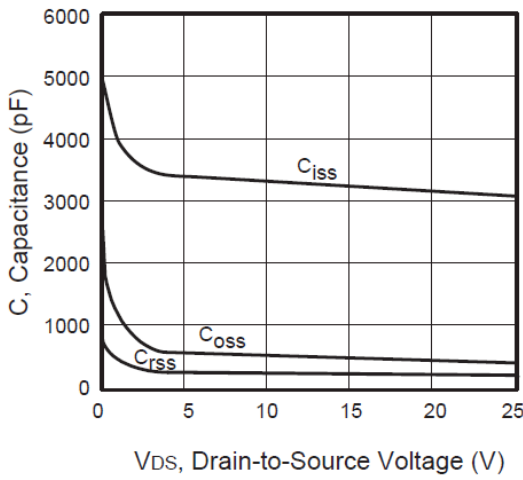


Figure 3. Capacitance

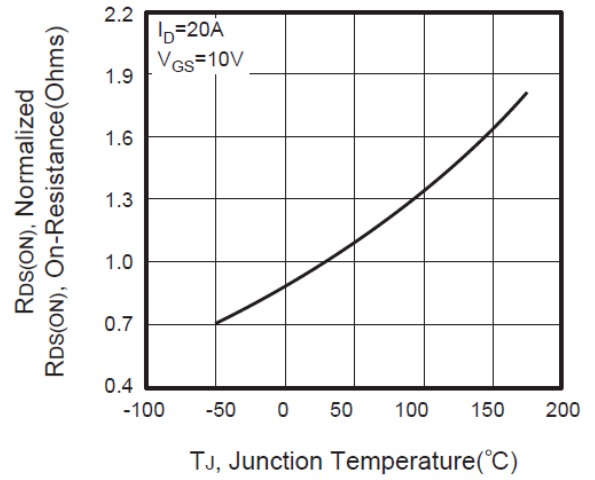


Figure 4. On-Resistance Variation with Temperature

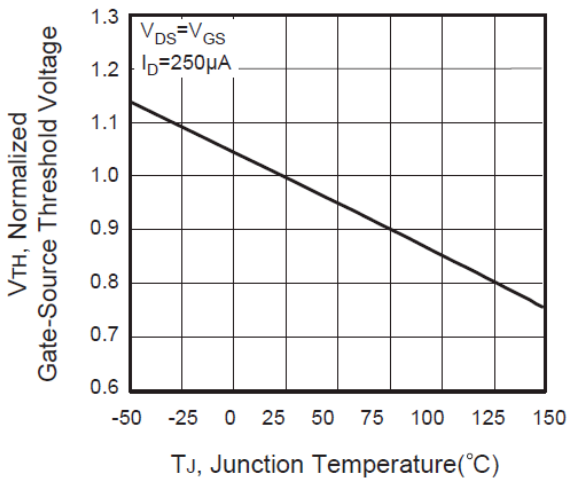


Figure 5. Gate Threshold Variation with Temperature

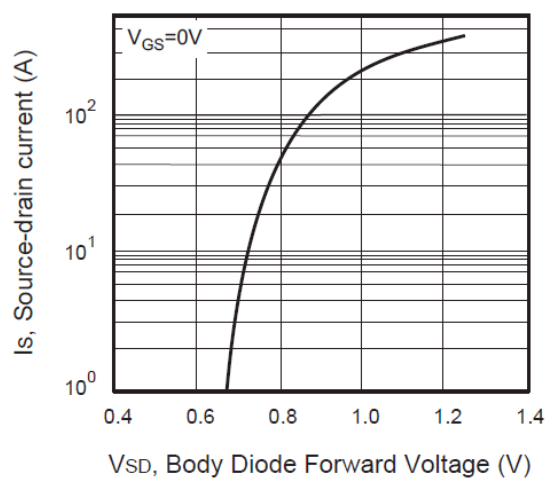


Figure 6. Body Diode Forward Voltage Variation with Source Current



ACE17427B N-Channel Enhancement Mode Power MOSFET

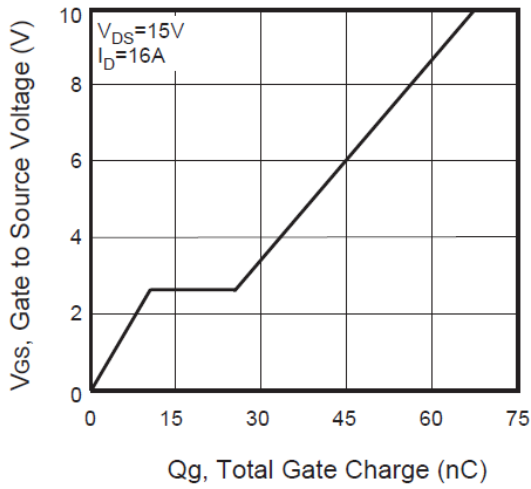


Figure 7. Gate Charge

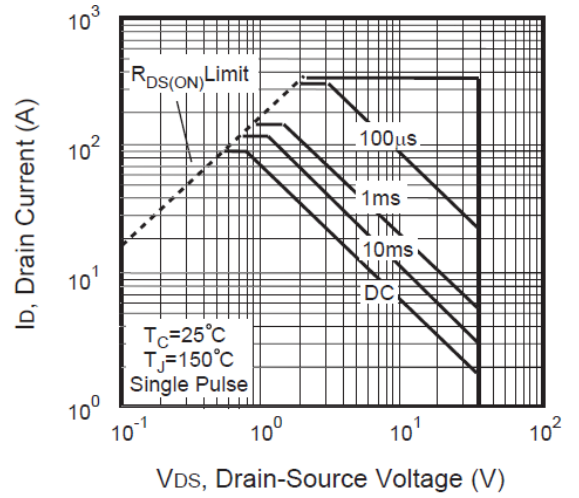


Figure 8. Maximum Safe Operating Area

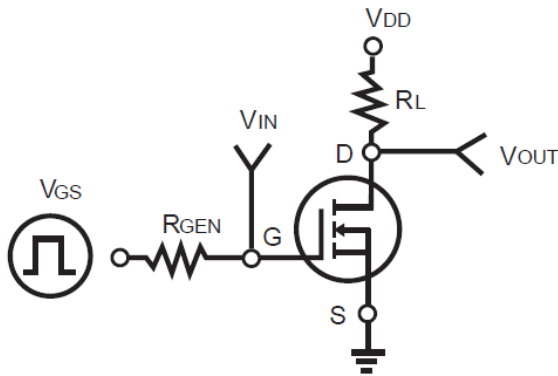


Figure 9. Switching Test Circuit

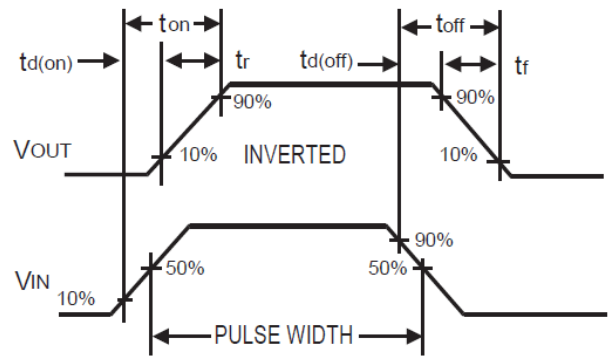


Figure 10. Switching Waveforms

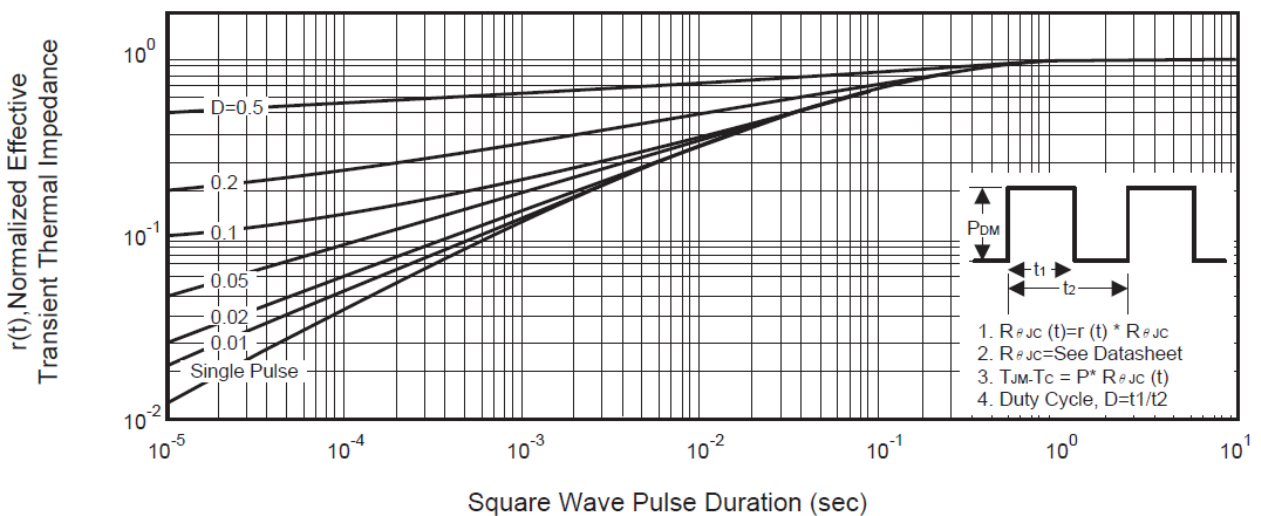


Figure 11. Normalized Thermal Transient Impedance Curve

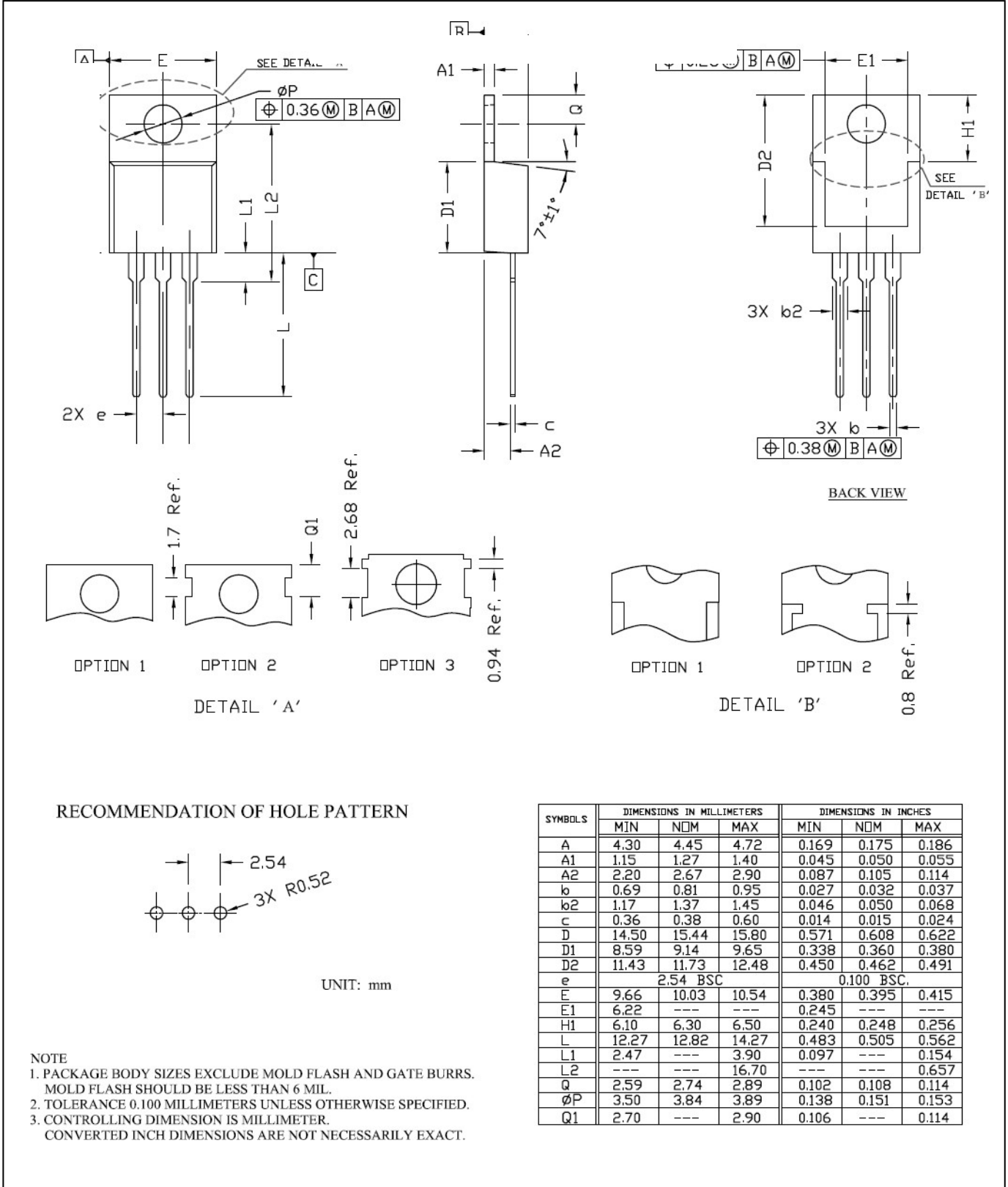


ACE17427B

N-Channel Enhancement Mode Power MOSFET

Packing Information

TO-220





ACE17427B

N-Channel Enhancement Mode Power MOSFET

Notes

ACE does not assume any responsibility for use as critical components in life support devices or systems without the express written approval of the president and general counsel of ACE Electronics Co., LTD. As used herein:

1. Life support devices or systems are devices or systems which, (a) are intended for surgical implant into the body, or (b) support or sustain life, and whose failure to perform when properly used in accordance with instructions for use provided in the labeling, can be reasonably expected to result in a significant injury to the user.
2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.